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Hole doping induced metal-insulator transition in $\text{Sr}_{1-x}\text{K}_x\text{IrO}_4$

QING'AN LI, QINGBIAO ZHAO, B.J. KIM, J.F. MITCHELL, Argonne National Laboratory — We report a metal-insulator transition against temperature in hole doped Sr_2IrO_4 . The temperature dependence of *ab*-plane resistivity of the doped Sr_2IrO_4 shows a peak at 6.5K. The magnetization against temperature shows a magnetic transition temperature about 200 K that is significantly reduced compared with its pristine material (240K). Hall effect measurements confirm that the conduction carrier is hole. A small magnetoresistance $\sim 3.5\%$ with significant anisotropy with respect to magnetic field orientation is observed, indicating the importance of spin-orbital coupling on conduction mechanism of the materials.

Qing'an Li
Argonne National Laboratory

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